

<b>SPEC SHEET (FOR REFERENCE)</b>	Specification No.	Rev.	Page.
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**TYPE : 6PT3310N3T\*\***

CHIP SIZE	1.4 * 1.4mm
WAFER SIZE	6 inch
POSSIBLE DIE PER WAFER	7,550pcs

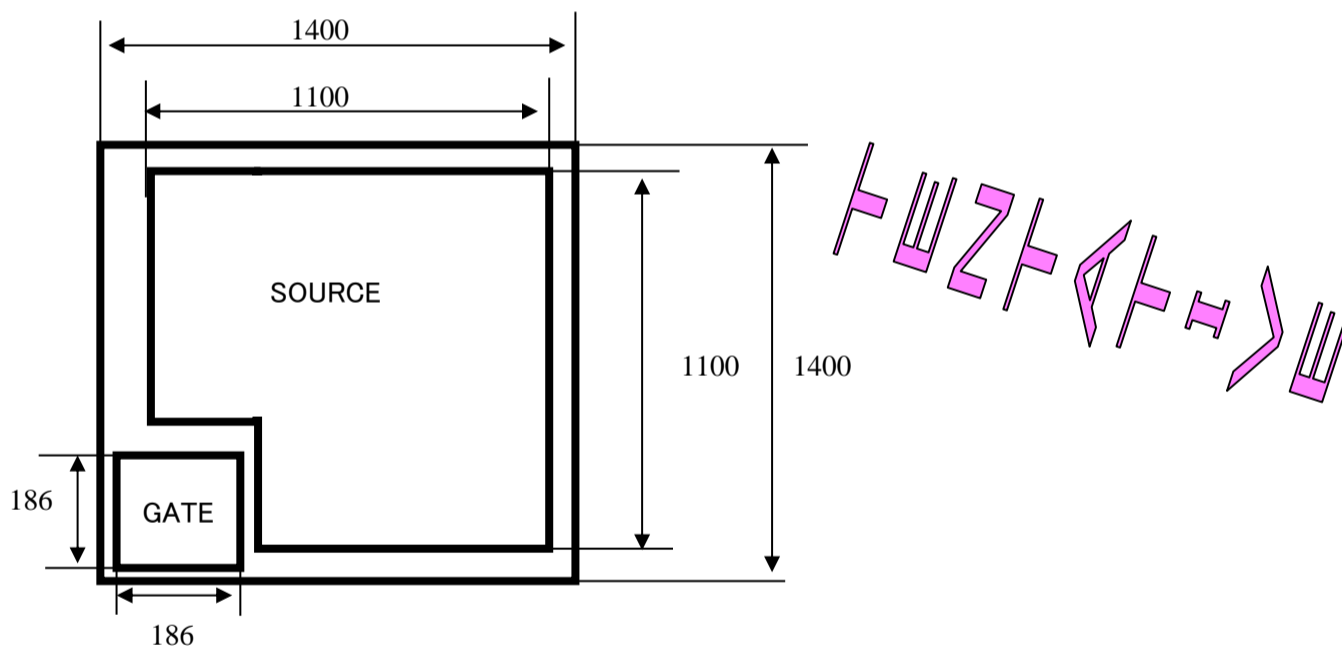
**Maximum Ratings(Ta=25°C)**

Characteristics	Symbol	Ratings	Unit
Drain-source voltage	VDSS	100	V
Gate-source voltage	VGSS	±20	V

**PROBING SPEC (Ta= 25C)**

No.	MODE	LIMIT				CONDITIONS
		MIN.	TYP.	MAX.	UNIT	
1	IGSS	-	±2	±10	uA	VGS= ±20V VDS=0V
2	IDSS	-		100	nA	VDS= 100V
3	BVDSS	105		-	V	ID= 10uA
4	Vth	1.5	2	2.5	V	ID= 250uA
5	RDS(on) 1	-	0.15	0.3	ohm	ID= 2.0A, VGS= 10V
6	RDS(on) 2	-	0.16	0.35	ohm	ID= 1.0A, VGS= 4.5V
7	VSD	0.5	0.75	1.1	V	IS= 1A, VGS= 0V
8	Yfs	500		-	mS	VDS= 10V, ID= 200mA

※ Built-in ZD between Gate and Source.



NOTE: